

XN1401

Silicon PNP epitaxial planer transistor

For general amplification

■ Features

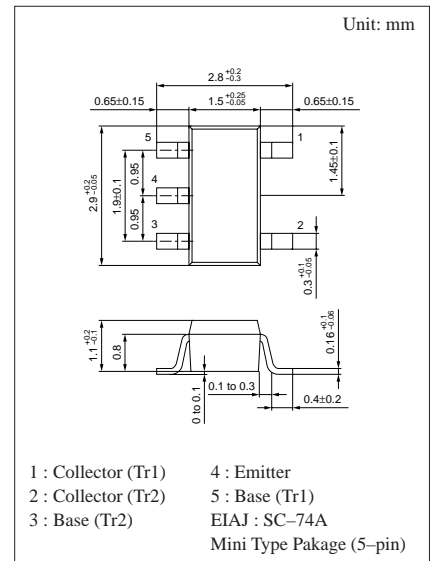
- Two elements incorporated into one package.
(Emitter-coupled transistors)
- Reduction of the mounting area and assembly cost by one half.

■ Basic Part Number of Element

- 2SB709A × 2 elements

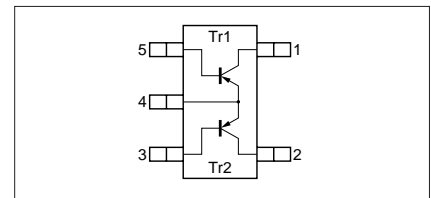
■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rated	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-100	mA
Peak collector current	I_{CP}	-200	mA
Total power dissipation	P_T	300	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{sig}	-55 to +150	°C



Marking Symbol: 5V

Internal Connection

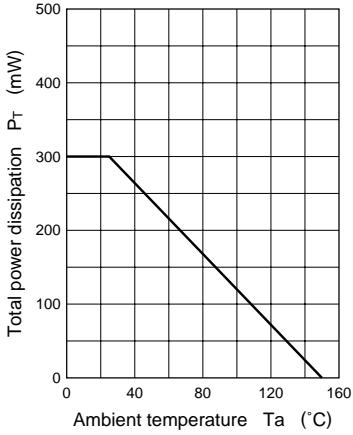


■ Electrical Characteristics (Ta=25°C)

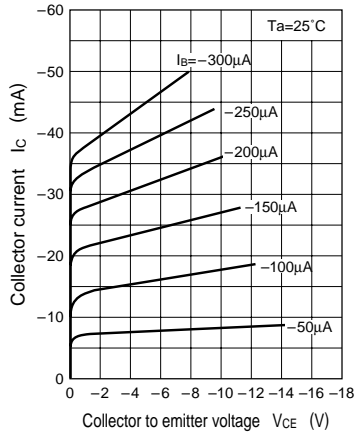
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V_{CBO}	$I_C = -10\mu A, I_E = 0$	-60			V
Collector to emitter voltage	V_{CEO}	$I_C = -2mA, I_B = 0$	-50			V
Emitter to base voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-7			V
Collector cutoff current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			-0.1	μA
	I_{CEO}	$V_{CE} = -10V, I_B = 0$			-100	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10V, I_C = -2mA$	160		460	
Forward current transfer h_{FE} ratio	$h_{FE}(\text{small/large})^{*1}$	$V_{CE} = -10V, I_C = -2mA$	0.5	0.99		
Collector to emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -100mA, I_B = -10mA$		-0.3	-0.5	V
Transition frequency	f_T	$V_{CB} = -10V, I_E = 1mA, f = 200MHz$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		2.7		pF

*1 Ratio between 2 elements

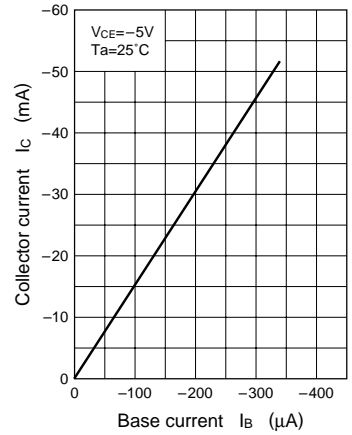
$P_T - T_a$



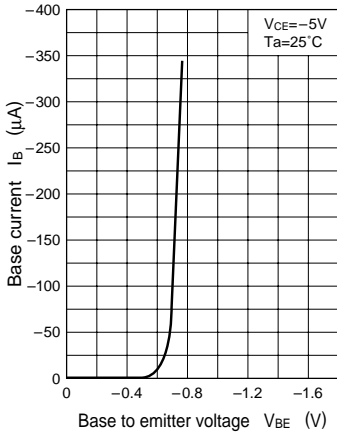
$I_C - V_{CE}$



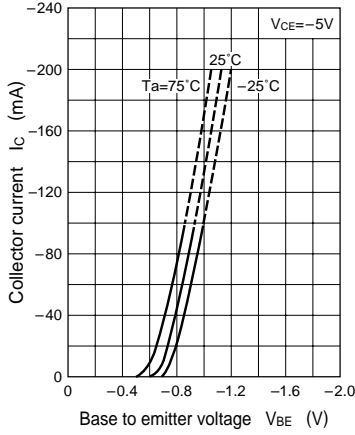
$I_C - I_B$



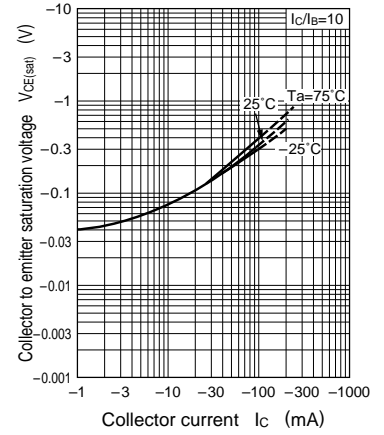
$I_B - V_{BE}$



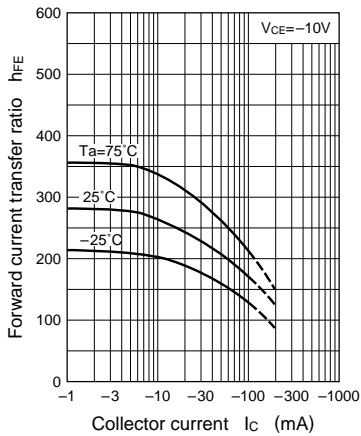
$I_C - V_{BE}$



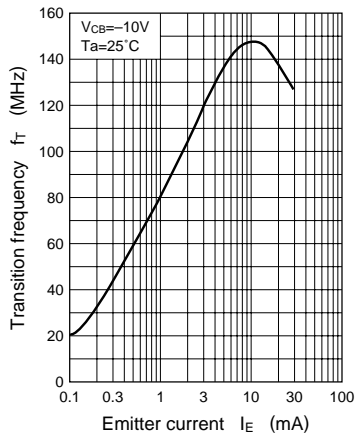
$V_{CE(sat)} - I_C$



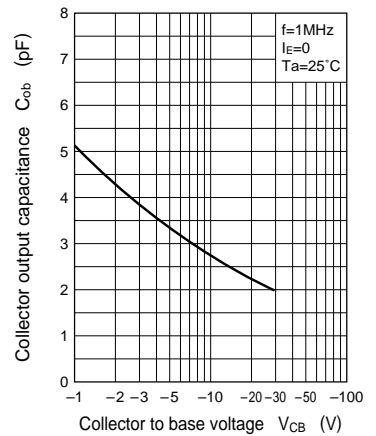
$h_{FE} - I_C$



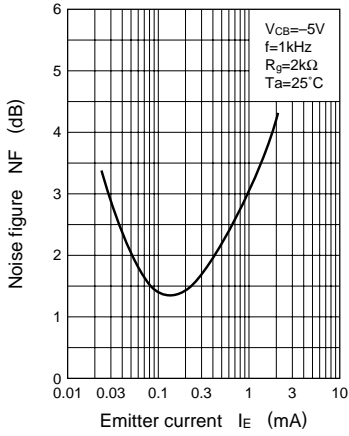
$f_T - I_E$



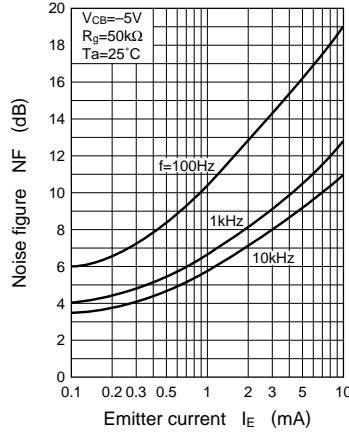
$C_{ob} - V_{CB}$



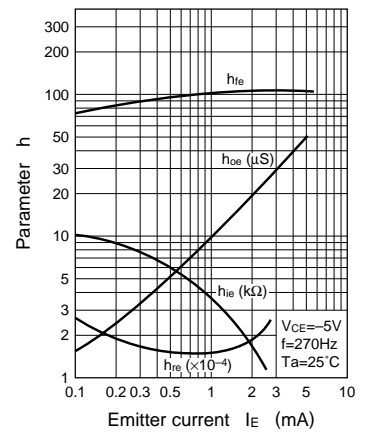
NF — I_E



NF — I_E



h Parameter — I_E



h Parameter — V_{CE}

